

Part Number

Customer

Category	Parameter	Specification	Measurement Method
OverallWafer	1.0 Diameter	100.00 +/- 0.50 mm	WaferVendor
	2.0 Primary Flat Orientation	<110> +/- 1 degree	Wafer Vendor
	3.0 Primary Flat Length	32.50 +/- 2.50 mm	Wafer Vendor
	4.0 Secondary Flat Orientation	none/semi	Wafer Vendor
	5.0 Overall Thickness	435.00 +/- 12.00 um	Guaranteed by Process
	6.0 Total Thickness Variation (TTV)	<5.00um	Guaranteed by Process
	7.0 Bow	<60.00um	Guaranteed by Process
	8.0 Warp	<60.00um	Guaranteed by Process
	9.0 Edge Exclusion	5 mm	Guaranteed by Process
HandleSilicon	10.0 Handle Growth Method	CZ	Wafer Vendor
	11.0 Handle Orientation	<100> +/- 1.0 degree	Wafer Vendor
	12.0 Handle Thickness	400.00 +/- 10.00 um	Guaranteed by Process
	13.0 Handle Doping Type	P	Wafer Vendor
	14.0 Handle Dopant	Boron	Wafer Vendor
	15.0 Handle Resistivity	0.01 ~ 2 Ohmcm	Wafer Vendor
	16.0 Backside Finish	Lapped/Etched with lasermark and no oxide.	Guaranteed by process
DeviceSilicon	17.0 Device Growth Method	FZ	Wafer Vendor
	18.0 Device Orientation	<111> +/- 1.0 degree	Wafer Vendor
	19.0 Nominal Thickness	35.00 +/- 1.00 um	ADE Single Point, 100%
	20.0 Distance to device silicon edge from wafer edge	<= 2mm	Guaranteed by Process
	21.0 Device Doping Type	P	Wafer Vendor
	22.0 Device Dopant	Boron	Wafer Vendor
	23.0 Device Resistivity	1000 - 2000 Ohmcm	Wafer Vendor
	24.0 Buried Layer Implant	Energy = 40keV, Dose = 1e14, Species = Boron	Implant Vendor
	25.0 Voids	none	Guaranteed by Process, SAM inspection
	26.0 Haze	none	Guaranteed by Process, Bright Light inspection
	27.0 Scratches	none	Guaranteed by Process, Bright Light inspection

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Shipping Details	Wafer per box :	Max 25
	Packaging :	Taped Polypropylene Wafer Box Empak, Ultrapak, 100.00mm Antistatic Double Bagging
	Lot Shipment Data	Device Thickness Bow / Warp Data Handle and SOI Thickness



Explanatory Notes 1. Microscope inspection performed using microscope scan as below. 5x objective.

2. All bright light inspections performed exclude all wafer area outside the edge exclusion defined in Overall Wafer, Edge Exclusion. High intensity bright lamp inspection as per ASTM F523.

3. 9 point measurement are as shown in the diagram below:



Additional Information